

Description

The AO3401-HXY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = -30V I_D = -4.2A$ $R_{DS(ON)} < 54m\Omega@V_{GS} = 10V$ $R_{DS(ON)} < 77m\Omega@V_{GS} = 4.5V$

Application

Battery protection Load switch Uninterruptible power supply

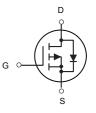
Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AO3401-HXY	SOT23-3L	X1KX	3000

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	-30	V
Vgs	Gate-Source Voltage	±12	V
Ι _D	Drain Current-Continuous	-4.2	A
Ідм	Drain Current-Pulsed (Note 1)	-30	A
PD	Maximum Power Dissipation	1.2	W
Тј,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	104	°C /W





P-Channel MOSFET



Electrical Characteristics (T_A=25°C unless otherwise noted)

Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-24V, V_{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250µA	-0.7	-1	-1.3	V
	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.2A	-	46	54	mΩ
Drain-Source On-State Resistance		V _{GS} =-4.5V, I _D =-4A	-	58	77	mΩ
		V _{GS} =-2.5V, I _D =-1A		74	130	mΩ
Forward Transconductance	g fs	V _{DS} =-5V,I _D =-4.2A	-	10	_	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =-15V,V _{GS} =0V, F=1.0MHz	-	880	-	PF
Output Capacitance	C _{oss}		-	105	-	PF
Reverse Transfer Capacitance	C _{rss}		-	65	_	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	7	-	nS
Turn-on Rise Time	tr	V _{DD} =-15V,I _D =-4.2A	-	3	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10V,R _{GEN} =6 Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Qg	V _{DS} =-15V,I _D =-4.2A,V _{GS} =-4.5V	-	8.5	_	nC
Gate-Source Charge	Q _{gs}		-	1.8	-	nC
Gate-Drain Charge	Q _{gd}		-	2.7	-	nC
Drain-Source Diode Characteristics		•				
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-4.2A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

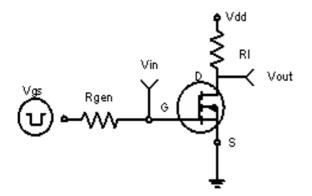
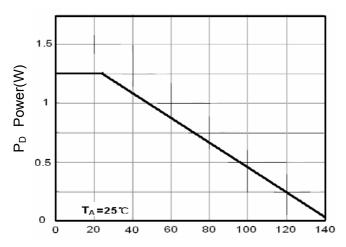
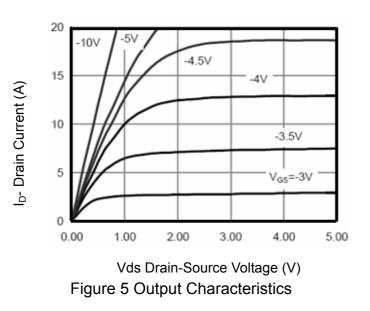


Figure 1:Switching Test Circuit



T_J-Junction Temperature(℃) Figure 3 Power Dissipation



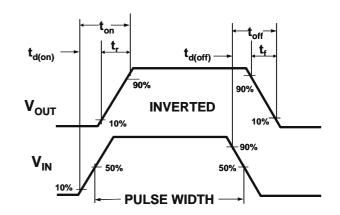
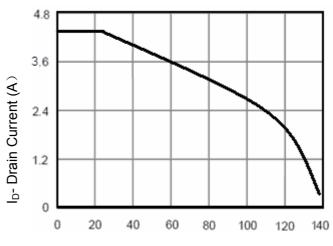


Figure 2:Switching Waveforms



T_J-Junction Temperature(℃) Figure 4 Drain Current

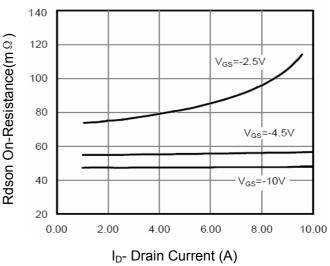
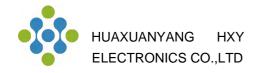
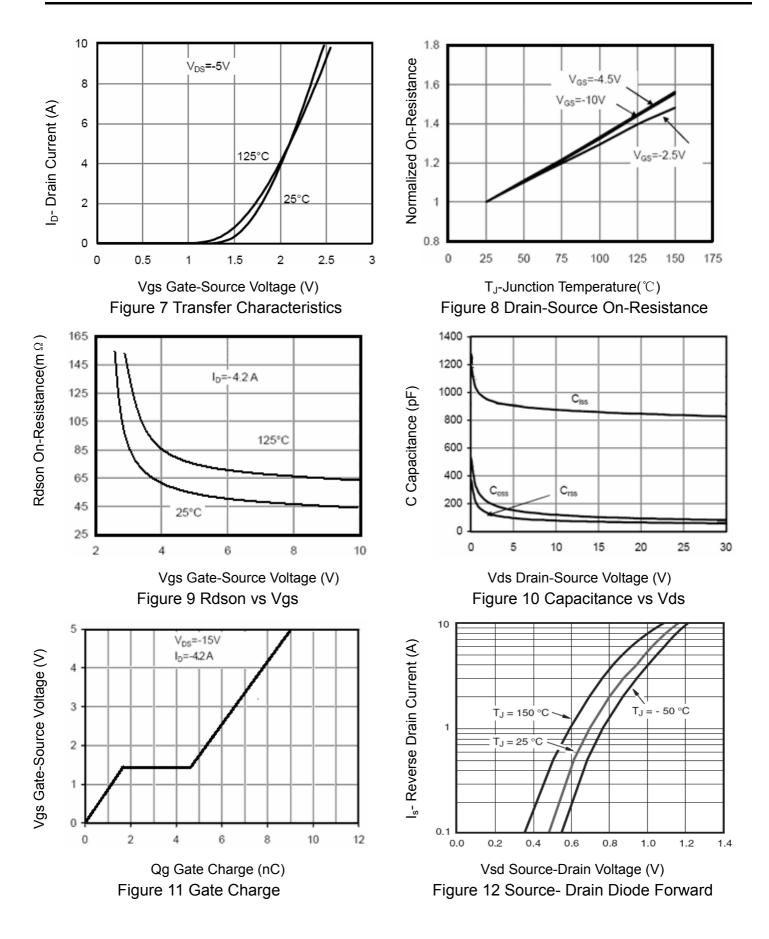
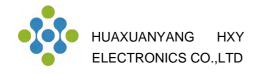
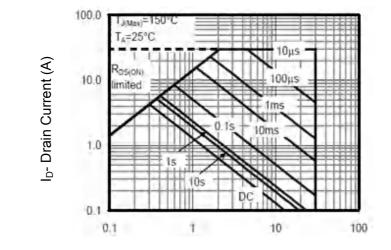


Figure 6 Drain-Source On-Resistance

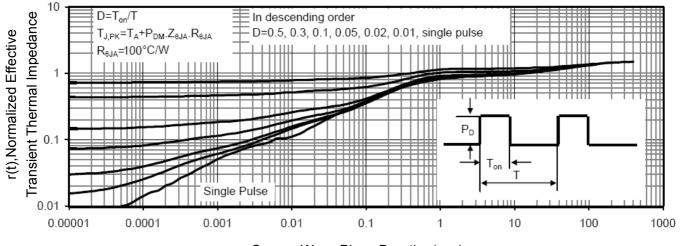




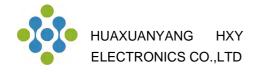




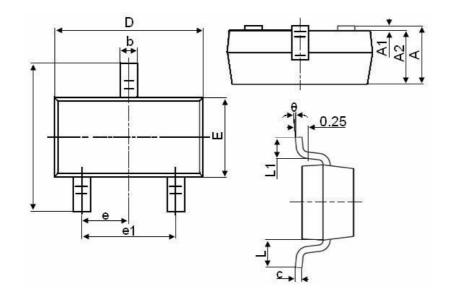
Vds Drain-Source Voltage (V) Figure 13 Safe Operation Area



Square Wave Pluse Duration(sec) Figure 14 Normalized Maximum Transient Thermal Impedance



SOT23-3L Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
A	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
с	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е	0.950TYP		
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	



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